
2SH31

Silicon N Channel IGBT
High Speed Power Switching

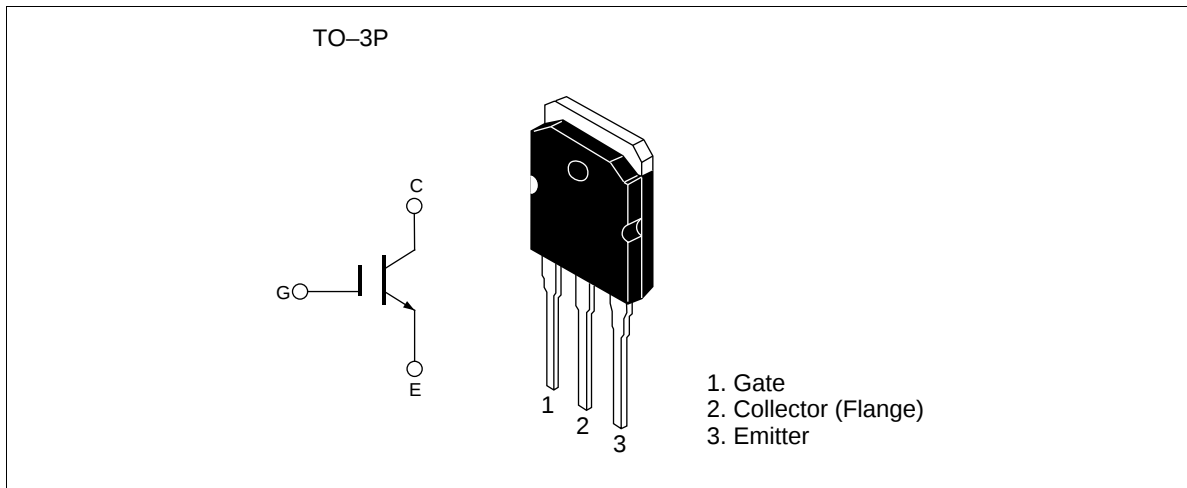
HITACHI

ADE-208-793(Z)
1st. Edition
May 1999

Features

- High speed switching
- Low on-voltage

Outline



2SH31

Absolute Maximum Ratings (Ta = 25°C)

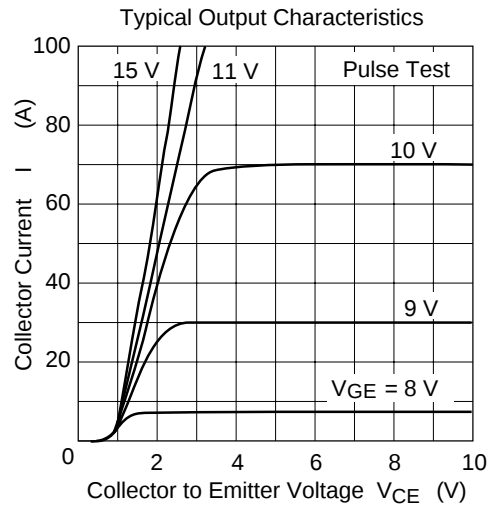
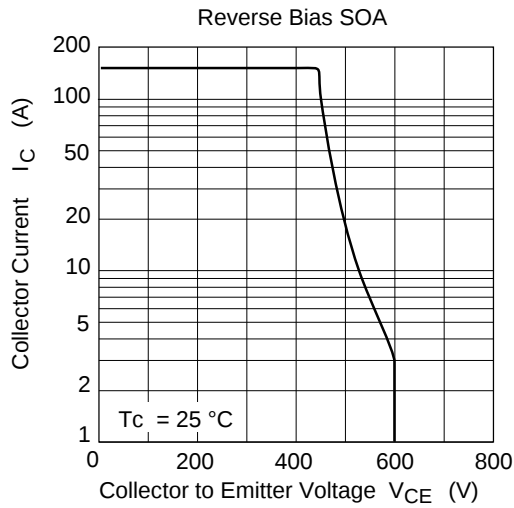
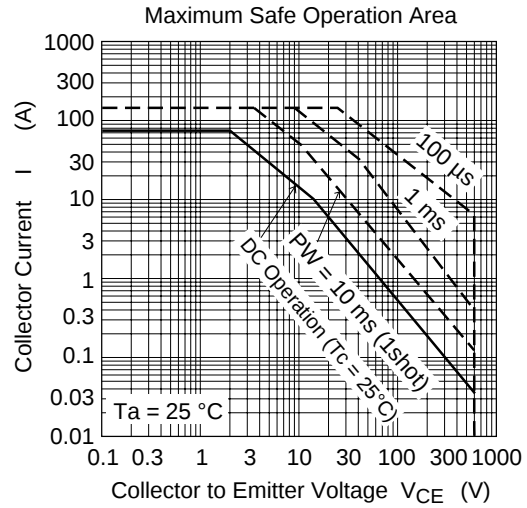
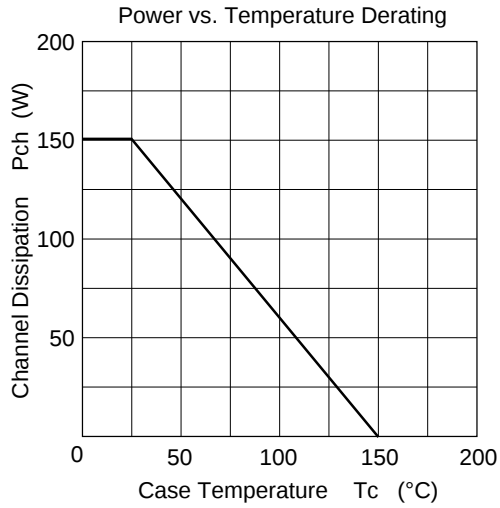
Item	Symbol	Ratings	Unit
Collector to Emitter voltage	V_{CES}	600	V
Gate to Emitter voltage	V_{GES}	± 20	V
Collector current	I_C	75	A
Collector peak current	$i_c(\text{peak})$	150	A
Collector dissipation	P_C ^{Note1}	150	W
Channel temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

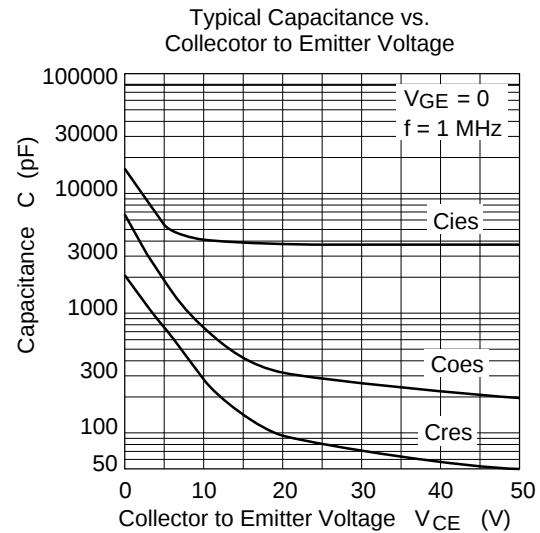
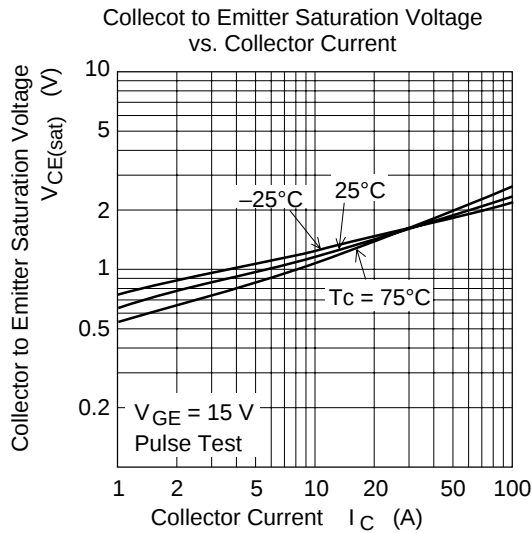
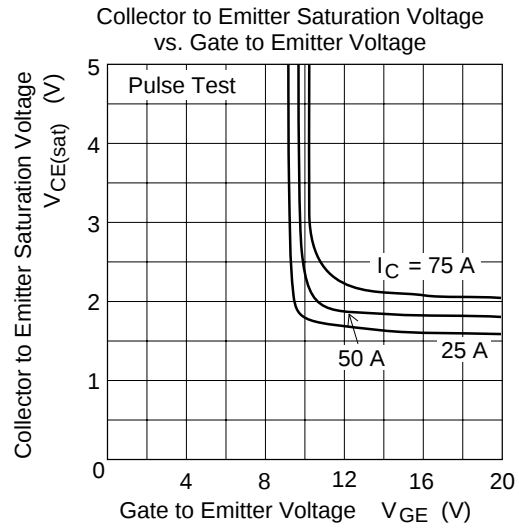
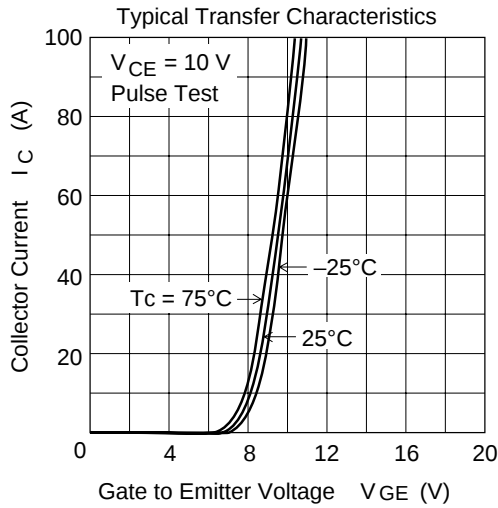
Note: 1. Value at $T_c = 25^\circ\text{C}$

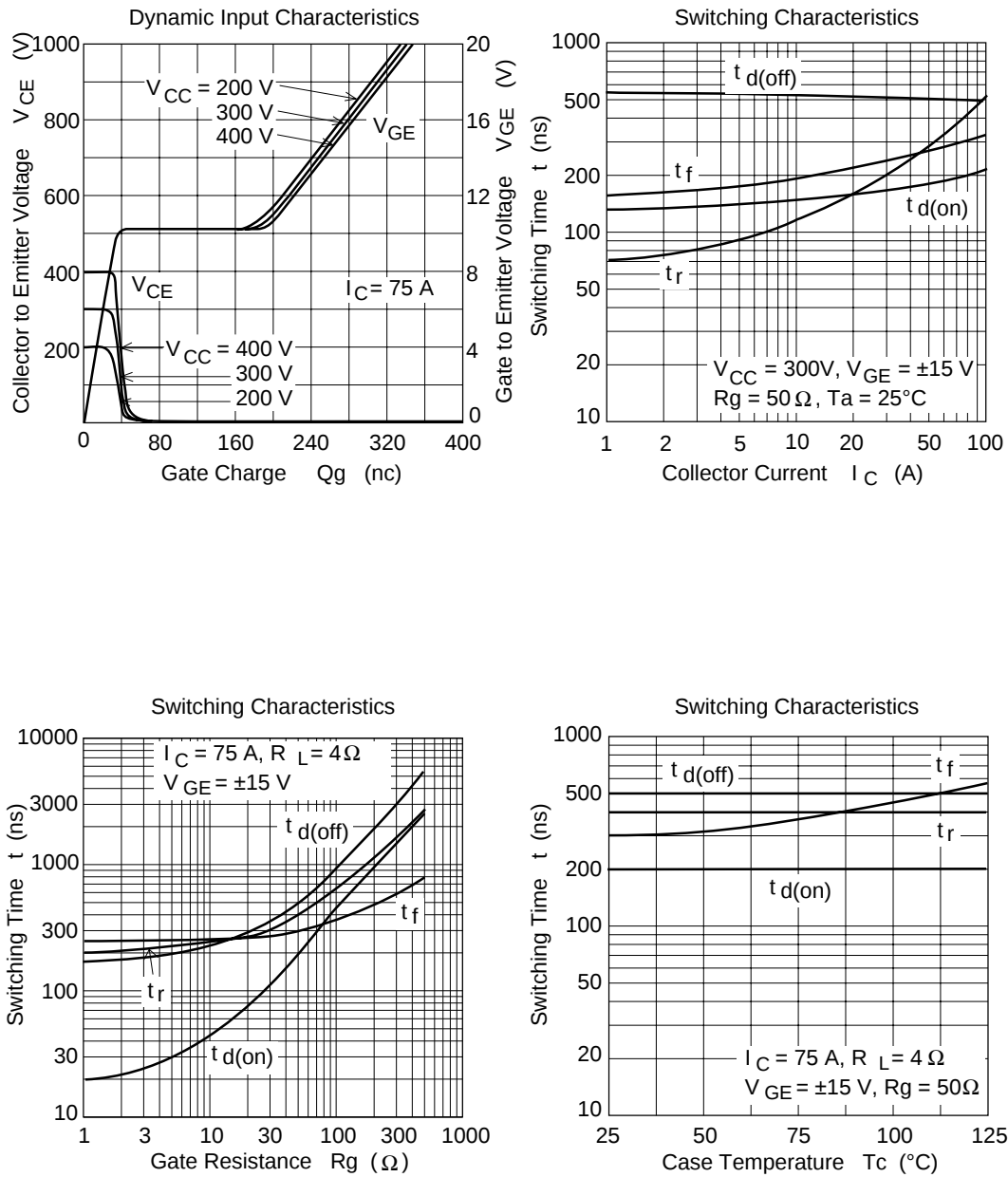
Electrical Characteristics (Ta = 25°C)

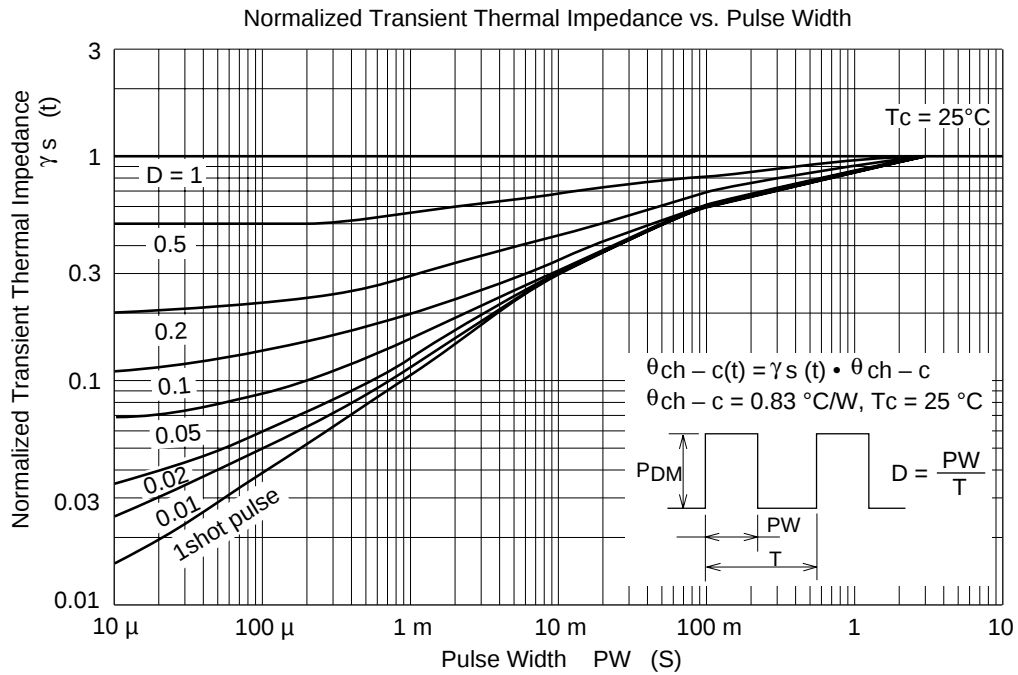
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage collector current	I_{CES}	—	—	100	μA	$V_{CE} = 600\text{V}$, $V_{GE} = 0$
Gate to emitter leak current	I_{GES}	—	—	± 1	μA	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(\text{off})}$	6.0	—	8.0	V	$I_C = 75\text{mA}$, $V_{CE} = 10\text{V}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	2.1	2.6	V	$I_C = 75\text{A}$, $V_{GE} = 15\text{V}$
Input capacitance	C_{ies}	—	4100	—	pF	$V_{CE} = 10\text{V}$, $V_{GE} = 0$ $f = 1\text{MHz}$
Switching time	t_r	—	400	—	ns	$I_C = 75\text{A}$
	t_{on}	—	600	—	ns	$R_L = 4\ \Omega$
	t_f	—	300	600	ns	$V_{GS} = \pm 15\text{V}$
	t_{off}	—	800	1600	ns	$R_g = 50\ \Omega$

Main Characteristics

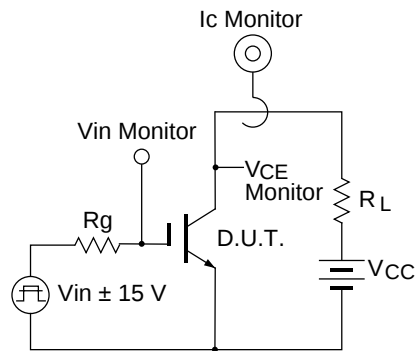




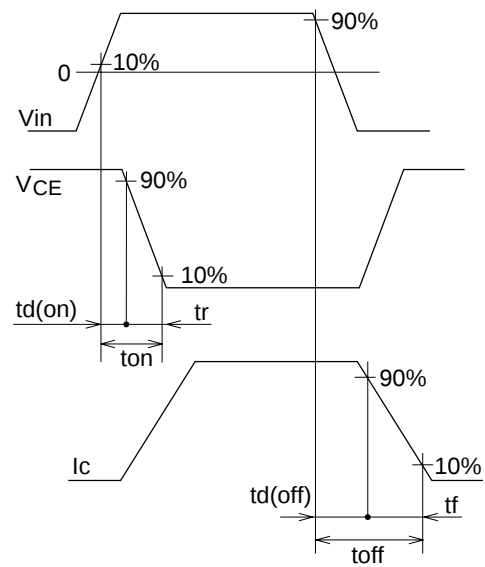




Switching Time Test Circuit

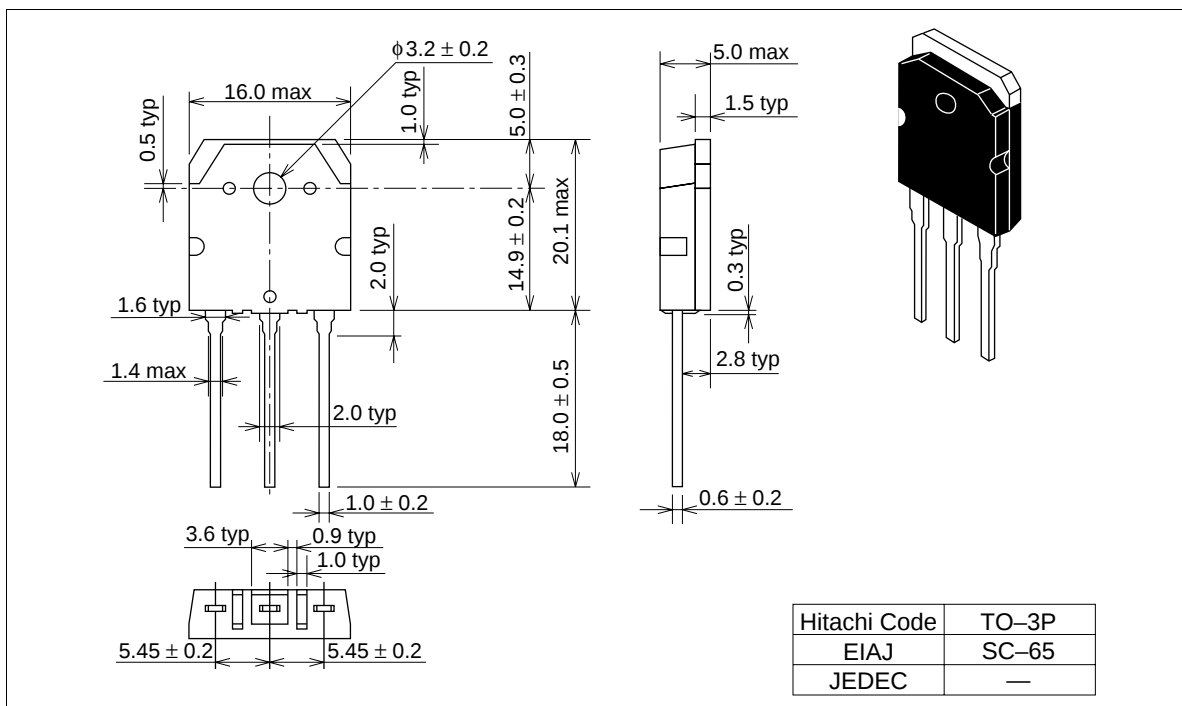


Waveform



Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Domacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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